Vincotech

10-PZ126PA075ME-M909F38Y
datasheet

***flow*PACK 0 SiC** **1200 V / 75 mΩ**

Topology features

- 3xHalf Bridge
- Open Emitter configuration
- Kelvin Emitter for improved switching performance
- Integrated DC capacitor
- Split output for transient deactivation of the body diode and elimination of X-conduction at fast turn-on
- Temperature sensor

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Al_2O_3
- Clip-in, reliable mechanical connection, qualified for wave soldering
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

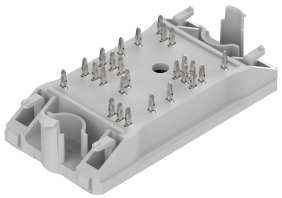
Target applications

- Power Supply
- Solar Inverters

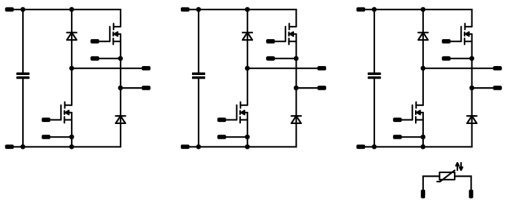
Types

- 10-PZ126PA075ME-M909F38Y

flow 0 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Drain-source voltage	V_{DSS}		1200	V
Drain current (DC current)	I_D	T_j = T_{jmax} T_s = 80 °C	21	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	80	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	52	W
Gate-source voltage	V_{GSS}	static	-4 / 15	V
		dynamic	-8 / 19	V
Maximum Junction Temperature	T_{jmax}		175	°C
Inverter Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Forward current (DC current)	I_F	T_j = T_{jmax} T_s = 80 °C	19	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	53	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms T_j = 110 °C	81	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	45	W
Maximum junction temperature	T_{jmax}		175	°C
Capacitor (DC)				
Maximum DC voltage	V_{MAX}		1000	V
Operation Temperature	T_{op}		0 ... 125	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Creepage distance			>12,7	mm
Clearance			10,19	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Drain-source on-state resistance(1)	$r_{DS(on)}$		15		20	25 175		75 115	90	mΩ
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$			0,005	25	1,7	2,5	4	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		10	250	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25		1	100	µA
Internal gate resistance	r_g							10,5		Ω
Gate charge	Q_g		-4/15	800	20	25		54		nC
Short-circuit input capacitance	C_{iss}	f = 1 Mhz	0	1000	0	25		1350		pF
Short-circuit output capacitance	C_{oss}							58		
Reverse transfer capacitance	C_{rss}							3		
Diode forward voltage	V_{SD}		0		10	25		4,5		V
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,84		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 16 Ω R_{goff} = 16 Ω	-4/15	600	15	25 125 150		21,8 19,26 19,3		ns
Rise time	t_r					25 125 150		14,64 13,83 13,29		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		84,4 93,04 95,17		ns
Fall time	t_f					25 125 150		21,38 23,72 22,71		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,149 µC Q_{rFWD}=0,154 µC Q_{rFWD}=0,156 µC				25 125 150		0,262 0,244 0,242		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,081 0,08 0,083		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				10	25 125 150		1,3 1,47 1,54	1,8(1)	V
Reverse leakage current	I_R	V_r = 1200 V				25		2,8	500	µA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,12		K/W
Dynamic										
Peak recovery current	I_{RM}	di/dt=1350 A/µs di/dt=1270 A/µs di/dt=1158 A/µs	-4/15	600	15	25 125 150		8,78 9,57 9,72		A
Reverse recovery time	t_{rr}					25 125 150		32,27 30,66 30,52		ns
Recovered charge	Q_r					25 125 150		0,149 0,154 0,156		µC
Reverse recovered energy	E_{rec}					25 125 150		0,041 0,043 0,044		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		835,53 967,09 975,93		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Capacitor (DC)										
Static										
Capacitance	C	DC bias voltage = 0 V				25		47		nF
Tolerance							-10		10	%
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 499 Ω				100	3,2		3,3	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,3		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3380		K
Vincotech Thermistor Reference									V	

(1) Value at chip level

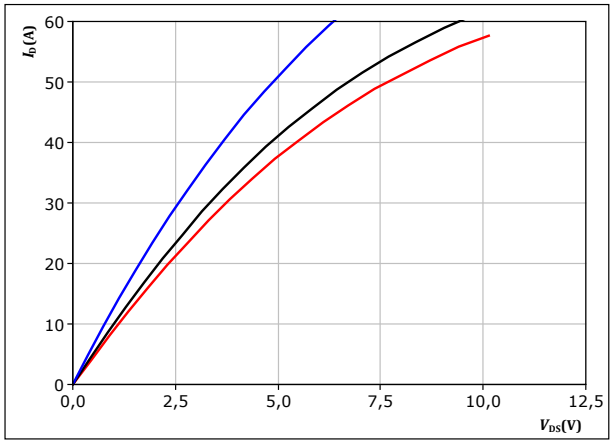
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **MOSFET**

Typical output characteristics including $R_{DD'} + R_{SS'}$

$I_D = f(V_{DS})$

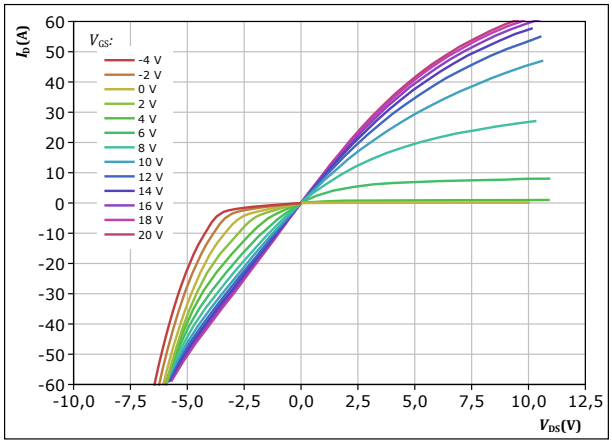


t_p =	250	µs	T_j:	25 °C
V_{GS} =	14	V		125 °C
				150 °C

figure 2. **MOSFET**

Typical output characteristics including $R_{DD'} + R_{SS'}$

$I_D = f(V_{DS})$



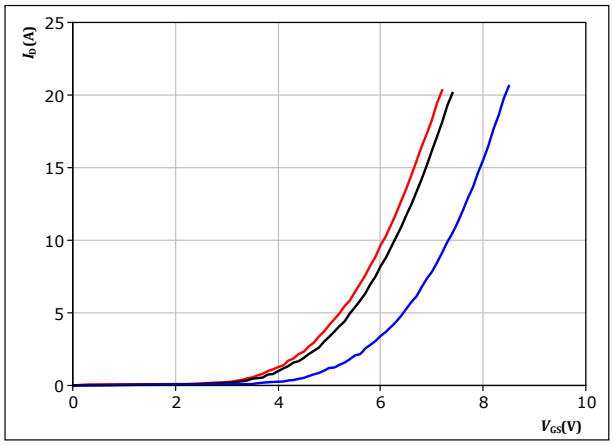
t_p =	250	µs
T_j =	150	°C

V_{GS} from -4 V to 20 V in steps of 2 V

figure 3. **MOSFET**

Typical transfer characteristics

$I_D = f(V_{GS})$

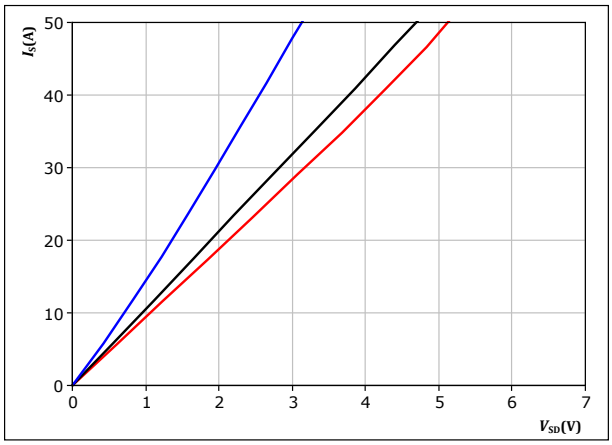


t_p =	250	µs	T_j:	25 °C
V_{DS} =	10	V		125 °C
				150 °C

figure 4. **MOSFET**

Typical reverse drain current characteristics including $R_{DD'} + R_{SS'}$

$I_{SD} = f(V_{SD})$



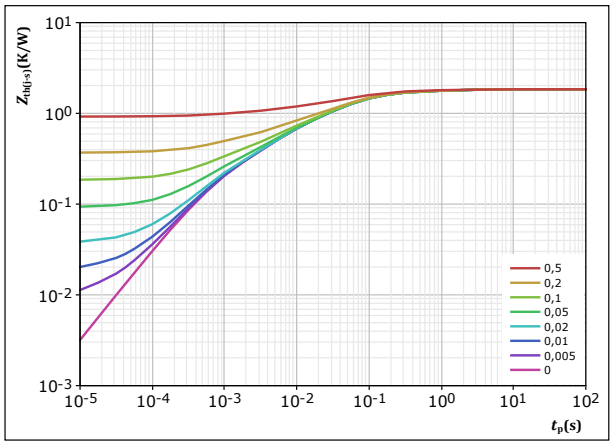
t_p =	250	µs	T_j:	25 °C
V_{GS} =	14	V		125 °C
				150 °C

Inverter Switch Characteristics

figure 5. **MOSFET**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	1,843	K/W

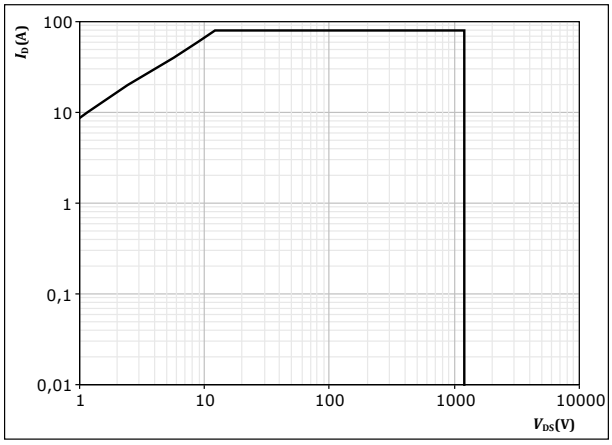
MOSFET thermal model values

R (K/W)	τ (s)
1,10E-01	1,89E+00
4,15E-01	1,55E-01
7,53E-01	3,96E-02
4,02E-01	6,20E-03
1,64E-01	7,03E-04

figure 6. **MOSFET**

Safe operating area

$I_D = f(V_{DS})$



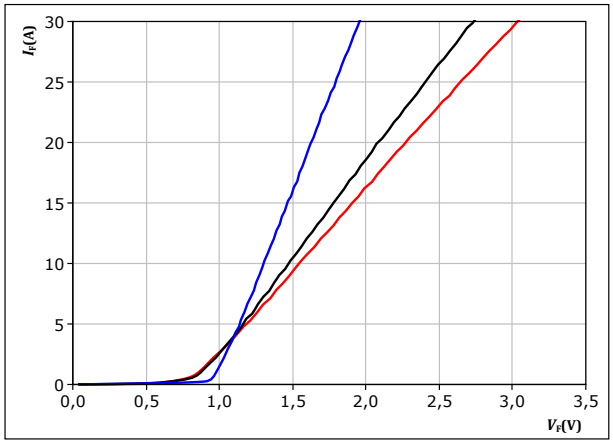
D =	single pulse	
T_s =	80	°C
V_{GS} =	14	V
T_j =	T_{jmax}	

Inverter Diode Characteristics

figure 7. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



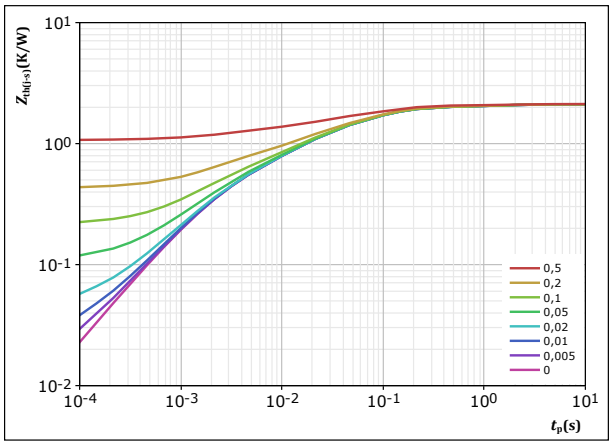
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 8. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 2,124 K/W

FWD thermal model values

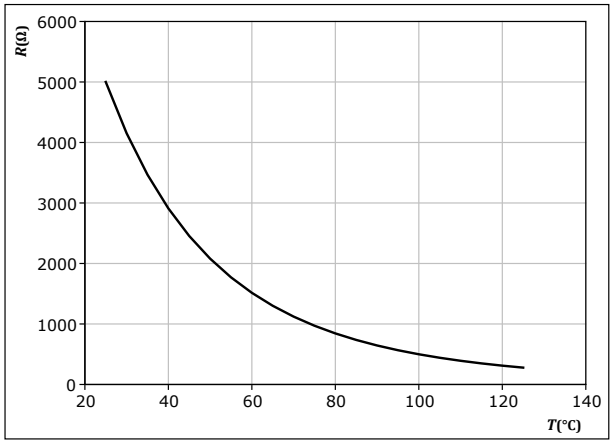
R (K/W)	τ (s)
2,40E-02	6,68E+01
1,38E-01	1,29E+00
9,33E-01	8,00E-02
6,88E-01	1,52E-02
3,52E-01	2,00E-03

Thermistor Characteristics

figure 9. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

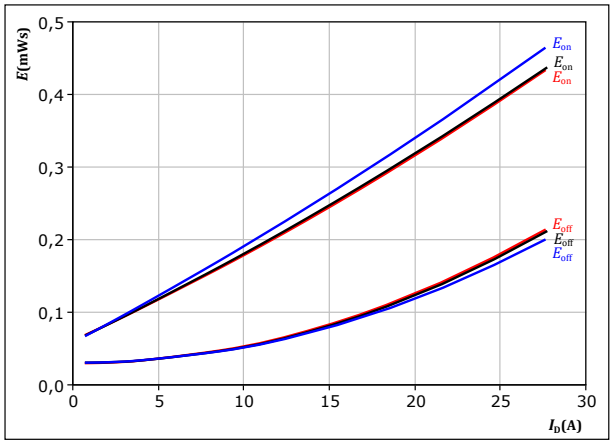


Inverter Switching Characteristics

figure 10. **MOSFET**

Typical switching energy losses as a function of drain current

$E = f(I_D)$



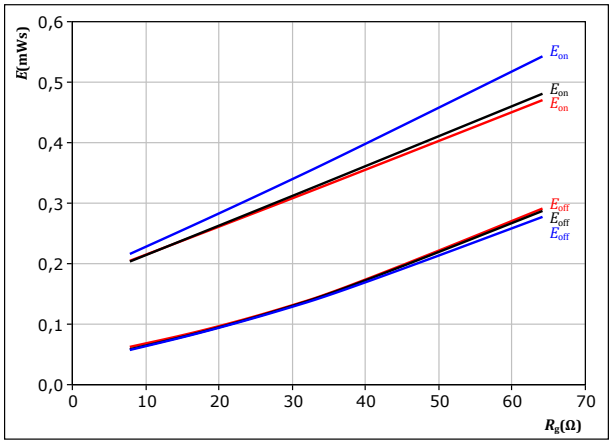
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
R_{gon} =	16	Ω		150 °C
R_{goff} =	16	Ω		

figure 11. **MOSFET**

Typical switching energy losses as a function of MOSFET turn on gate resistor

$E = f(R_g)$



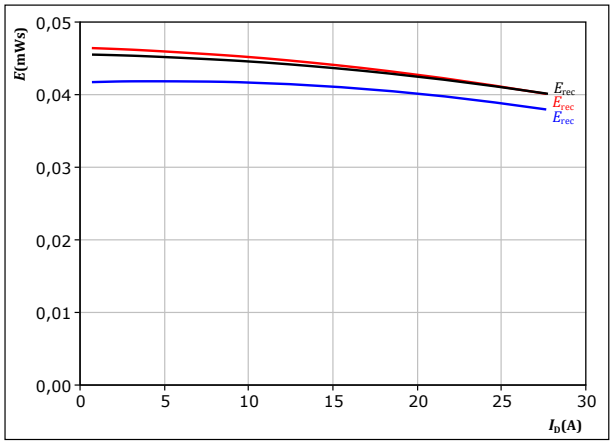
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
I_D =	15	A		150 °C

figure 12. **FWD**

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



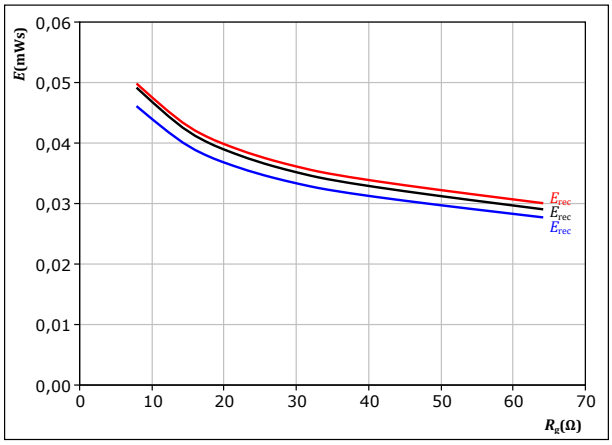
With an inductive load at

V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 13. **FWD**

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

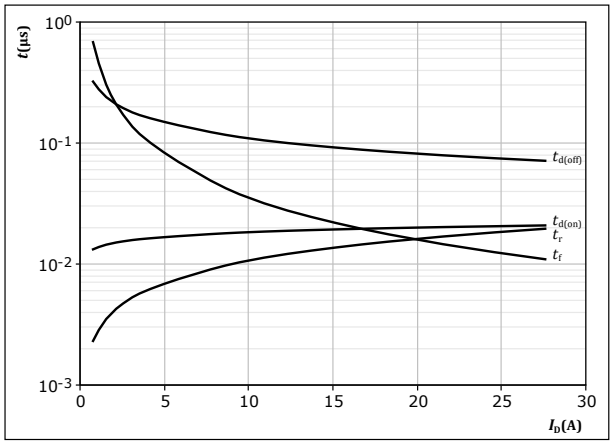
V_{DS} =	600	V	T_j:	25 °C
V_{GS} =	-4/15	V		125 °C
I_D =	15	A		150 °C

Inverter Switching Characteristics

figure 14. **MOSFET**

Typical switching times as a function of drain current

$t = f(I_D)$



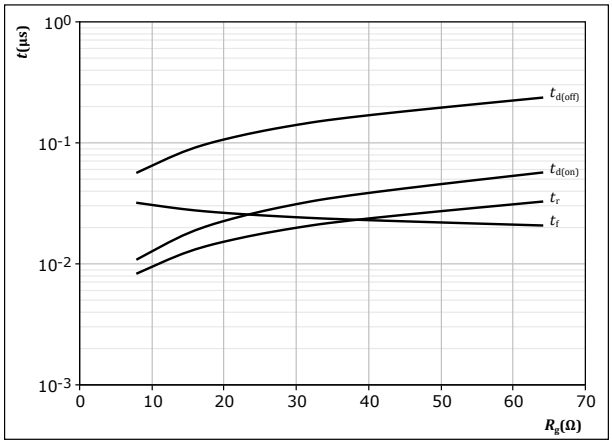
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-4/15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 15. **MOSFET**

Typical switching times as a function of MOSFET turn on gate resistor

$t = f(R_g)$



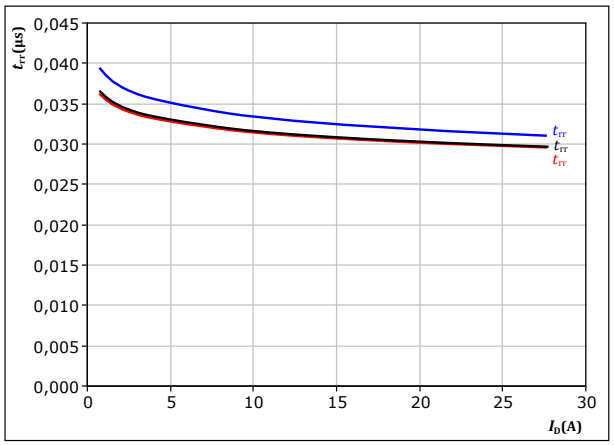
With an inductive load at

T_j =	150	°C
V_{DS} =	600	V
V_{GS} =	-4/15	V
I_D =	15	A

figure 16. **FWD**

Typical reverse recovery time as a function of drain current

$t_{rr} = f(I_D)$



At

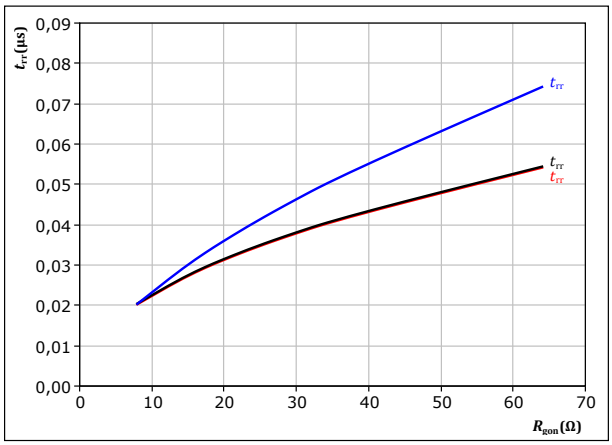
V_{DS} =	600	V
V_{GS} =	-4/15	V
R_{gon} =	16	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 17. **FWD**

Typical reverse recovery time as a function of MOSFET turn on gate resistor

$t_{rr} = f(R_{gon})$



At

V_{DS} =	600	V
V_{GS} =	-4/15	V
I_D =	15	A

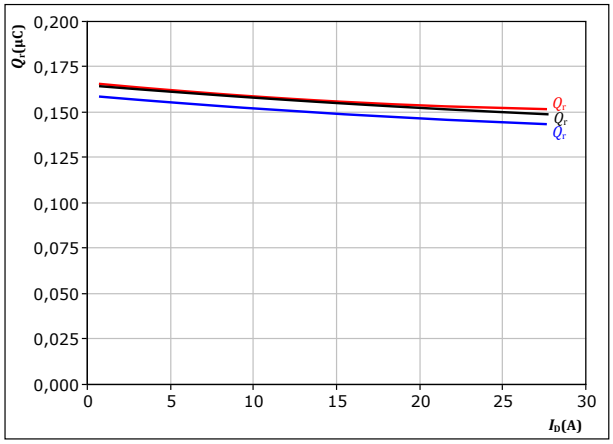
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 18. **FWD**

Typical recovered charge as a function of drain current

$Q_r = f(I_D)$

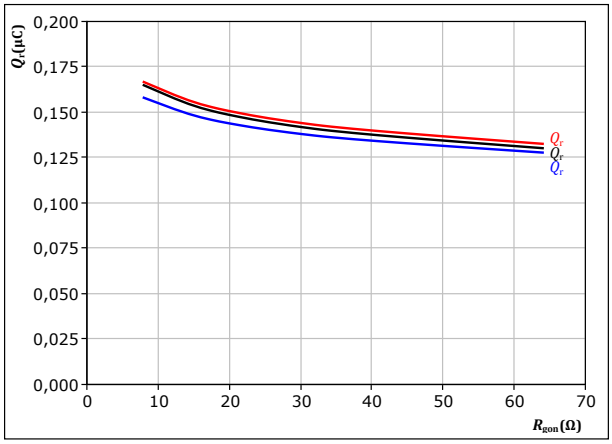


At				
V_{DS} =	600	V		
V_{GS} =	-4/15	V	T_j:	25 °C
R_{gon} =	16	Ω		125 °C
				150 °C

figure 19. **FWD**

Typical recovered charge as a function of MOSFET turn on gate resistor

$Q_r = f(R_{gon})$

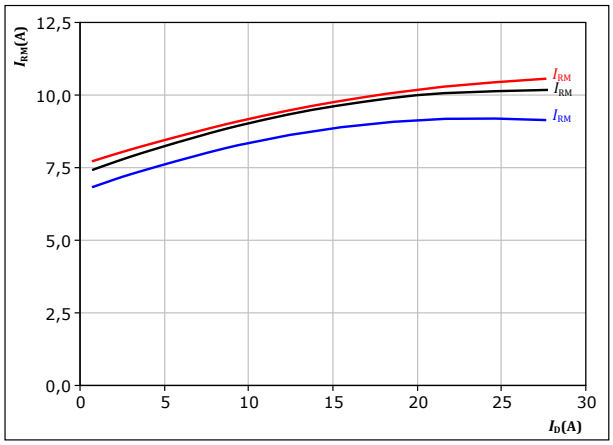


At				
V_{DS} =	600	V		
V_{GS} =	-4/15	V	T_j:	25 °C
I_D =	15	A		125 °C
				150 °C

figure 20. **FWD**

Typical peak reverse recovery current as a function of drain current

$I_{RM} = f(I_D)$

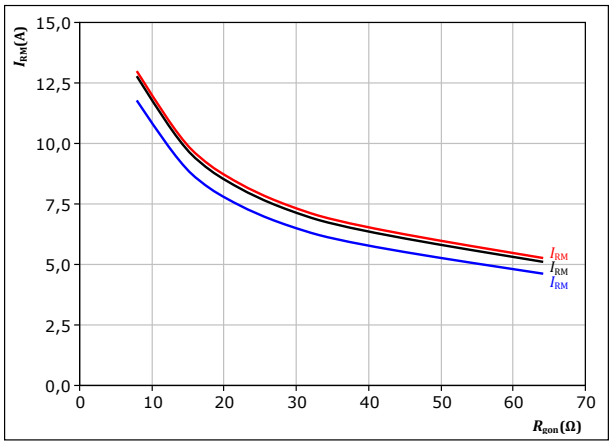


At				
V_{DS} =	600	V		
V_{GS} =	-4/15	V	T_j:	25 °C
R_{gon} =	16	Ω		125 °C
				150 °C

figure 21. **FWD**

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$I_{RM} = f(R_{gon})$



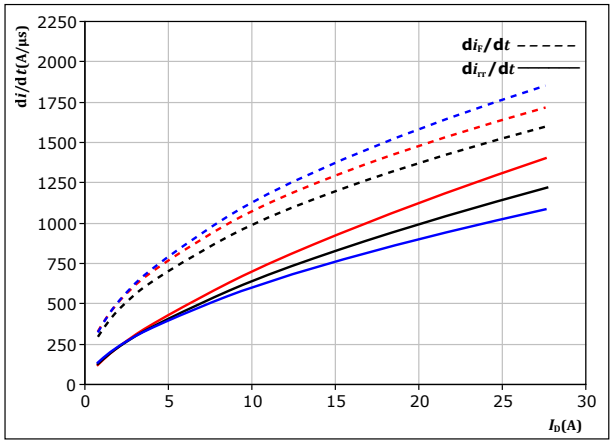
At				
V_{DS} =	600	V		
V_{GS} =	-4/15	V	T_j:	25 °C
I_D =	15	A		125 °C
				150 °C

Inverter Switching Characteristics

figure 22. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

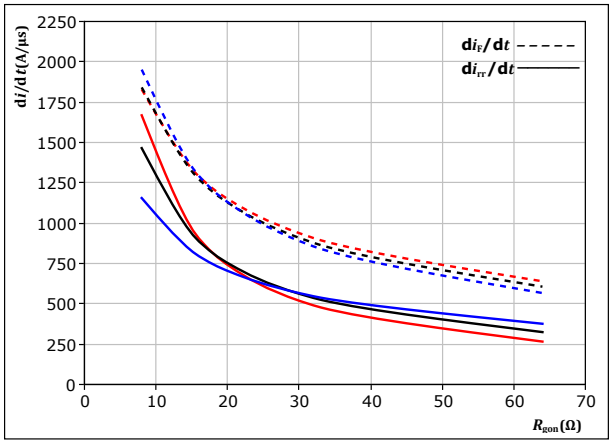


At					
	V_{DS} =	600	V		
	V_{GS} =	-4/15	V	T_j:	25 °C
	R_{gon} =	16	Ω		125 °C
					150 °C

figure 23. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

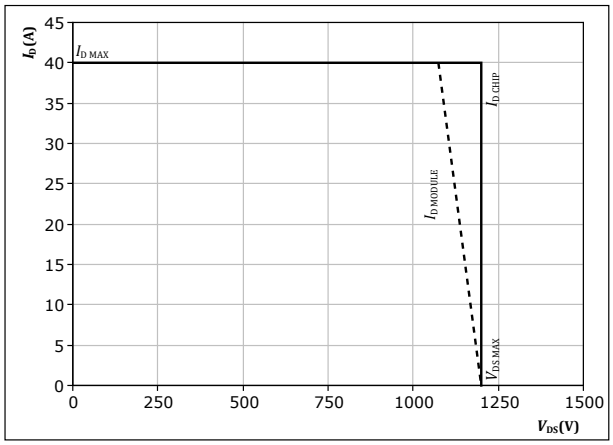


At					
	V_{DS} =	600	V		
	V_{GS} =	-4/15	V	T_j:	25 °C
	I_D =	15	A		125 °C
					150 °C

figure 24. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



At			
	T_j =	150	°C
	R_{gon} =	16	Ω
	R_{goff} =	16	Ω

Inverter Switching Definitions

figure 25. MOSFET

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})

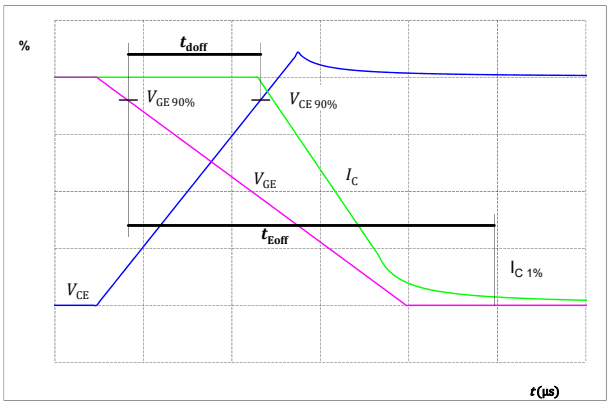


figure 26. MOSFET

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

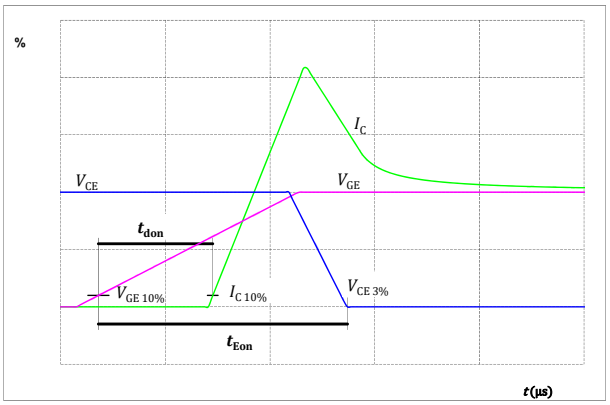


figure 27. MOSFET

Turn-off Switching Waveforms & definition of t_f

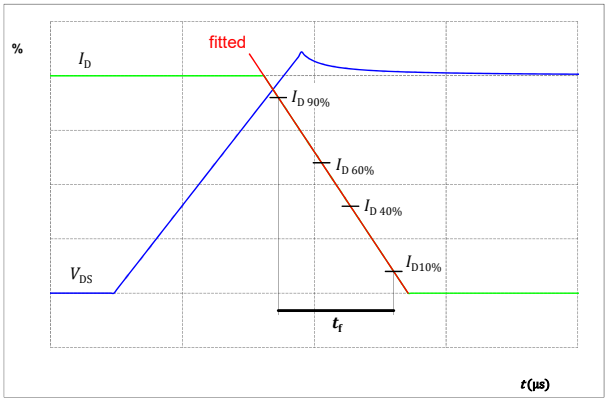
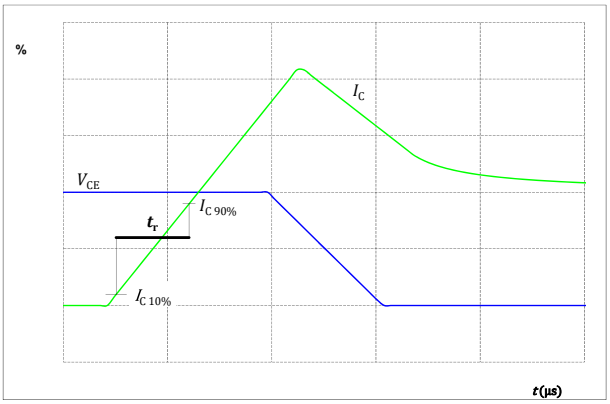


figure 28. MOSFET

Turn-on Switching Waveforms & definition of t_r



Inverter Switching Definitions

figure 29. **FWD**

Turn-off Switching Waveforms & definition of t_{trr}

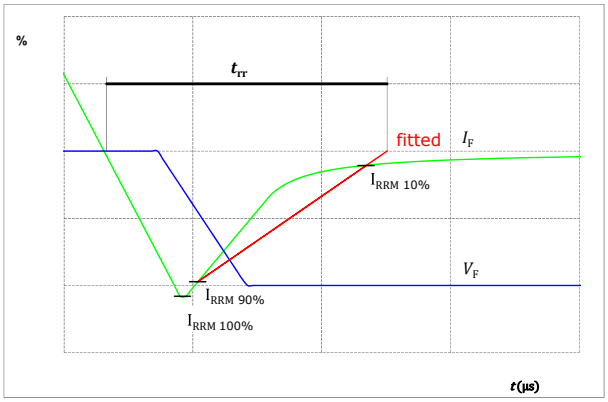


figure 30. **FWD**

Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})

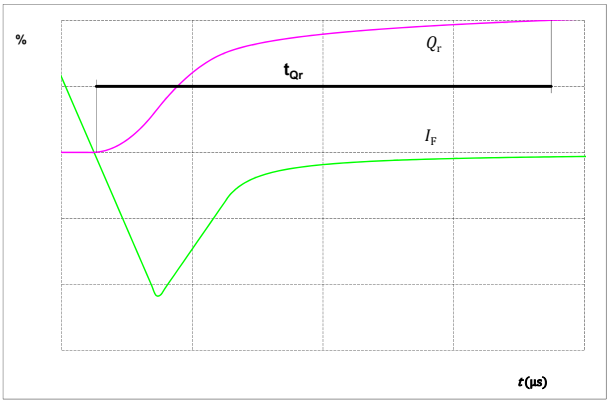
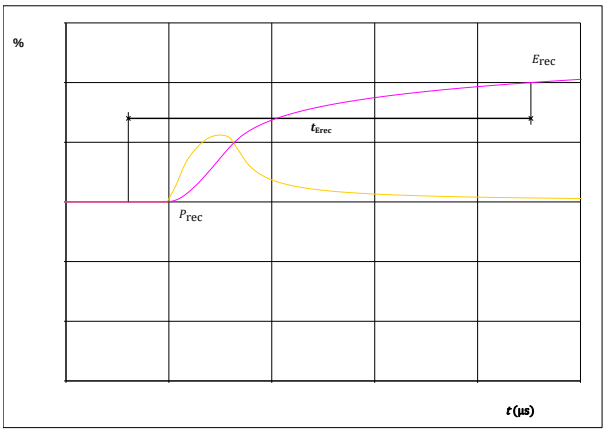


figure 31. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



Ordering Code

Version	Ordering Code
Without thermal paste	10-PZ126PA075ME-M909F38Y
With thermal paste (5,2 W/mK, PTM6000HV)	10-PZ126PA075ME-M909F38Y-/7/

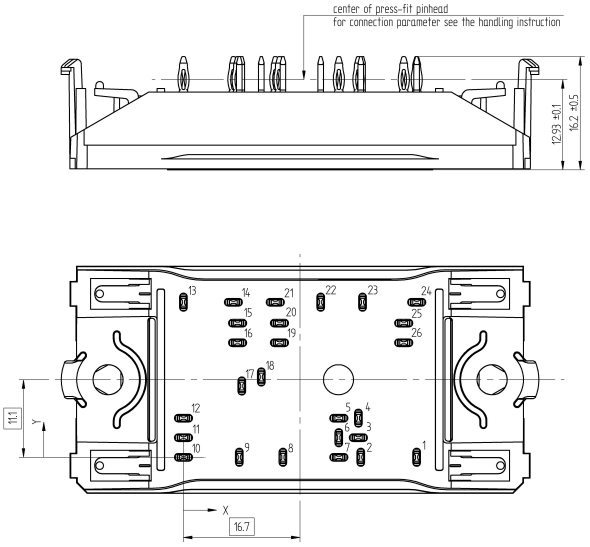
Marking

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTVV	LLLLL	SSSS	WWYY		

Outline

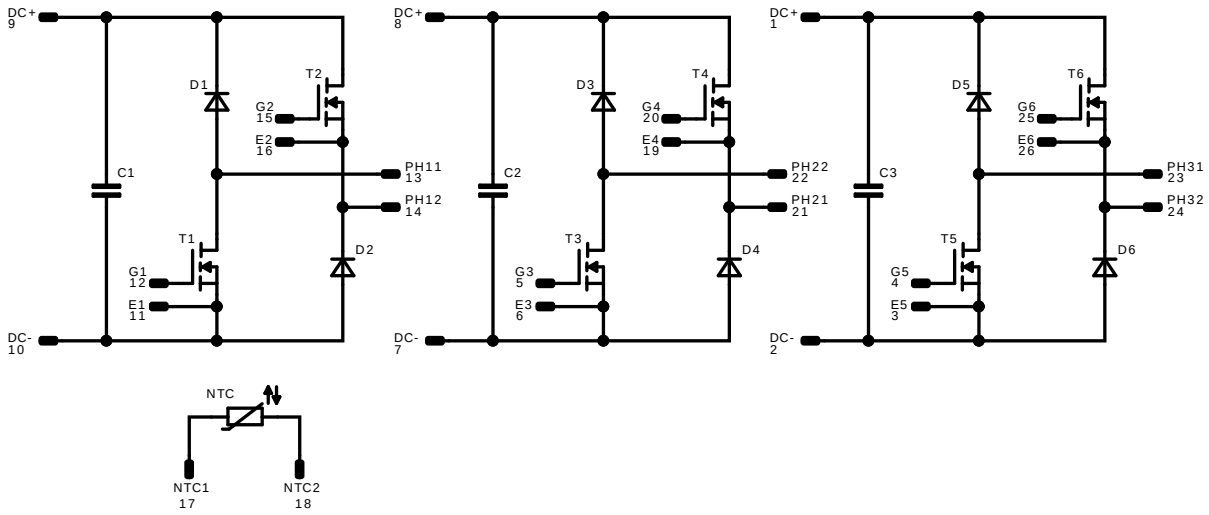
Pin table [mm]

Pin	X	Y	Function
1	33,4	0	DC+
2	25,4	0	DC-
3	25,05	2,8	E5
4	25,05	5,6	G5
5	22,25	5,6	G3
6	22,25	2,8	E3
7	22,25	0	DC-
8	14,25	0	DC+
9	8	0	DC+
10	0	0	DC-
11	0	2,8	E1
12	0	5,6	G1
13	0	22,2	PH11
14	7,15	22,2	PH12
15	7,75	19,2	G2
16	7,75	16,4	E2
17	8,35	10,2	NTC1
18	11,15	11,5	NTC2
19	13,75	16,4	E4
20	13,75	19,2	G4
21	13,15	22,2	PH21
22	19,65	22,2	PH22
23	25,65	22,2	PH31
24	33,4	22,2	PH32
25	31,55	19,2	G6
26	31,55	16,4	E6



Tolerance of pinpositions ±0.5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T1, T2, T3, T4, T5, T6	MOSFET	1200 V	75 mΩ	Inverter Switch	
D1, D2, D3, D4, D5, D6	FWD	1200 V	10 A	Inverter Diode	
C1, C2, C3	Capacitor	1000 V		Capacitor (DC)	
NTC	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-PZ126PA075ME-M909F38Y-D2-14	26 Oct. 2025	Change Inverter Diode according to PCN 2025-001	